

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	Unknown 10/788,810
Filing Date	Even Date Herewith 2-27-04
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2825
Examiner Name	Unknown Any

Sheet 1 of 5

Attorney Docket No: 1303.027US2

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Substitute Disclosure Statement Form (PTO-1449)

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First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2825
Examiner Name	Unknown Amy a

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Attorney Docket No: 1303.027US2

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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

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First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2825
Examiner Name	Unknown Amy M

Sheet 3 of 5

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**OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS**

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Substitute Disclosure Statement Form (PTO-1449)

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Complete if Known

Application Number	Unknown <b>6788, 810</b>
Filing Date	Even Date Herewith <b>2-22-04</b>
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown <b>2825</b>
Examiner Name	Unknown <b>Any a</b>

Sheet 4 of 5

Attorney Docket No: 1303.027US2

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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DATE CONSIDERED

8/4/04

Substitute Disclosure Statement Form (PTO-1446)

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10/788, 810

PTO/SB/08A (10-01)

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First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2825
Examiner Name	Unknown Amy V

Sheet 5 of 5

Attorney Docket No: 1303.027US2

## OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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Substitute Disclosure Statement Form (PTO-1449)

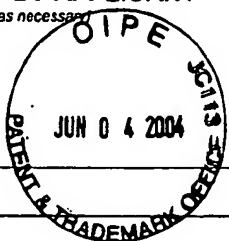
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First Named Inventor	Forbes, Leonard
Group Art Unit	<del>2812</del> 2828
Examiner Name	Unknown Any 9

Sheet 1 of 1

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1A	US-6,169,306	01/02/2001	Gardner, Mark I., et al.	257	310	07/27/1998

**FOREIGN PATENT DOCUMENTS**

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